


FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No.	Serial No.
		05-720-US2	10/559,981
		Applicant: Kouvetakis, et al.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		Filing Date:	Group:
		December 8, 2005	2812

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
RSP	1.	US 2003-0157787 A1	August 21, 2003	Murthy, et al.	—	—	
	2.	US 2006-0134895 A1	June 22, 2006	Kouvetakis, et al.	—	—	
	3.	US 2006-0236923 A1	October 26, 2006	Kouvetakis, et al.	—	—	
	4.	US 2006-0163612-A1	July 27, 2006	Kouvetakis, et al.	—	—	
	5.	6,911,084	June 28, 2005	Kouvetakis, et al.	—	—	
	6.	5,532,183	July 2, 1996	Sugawara, et al.	—	—	
	7.	5,198,387	March 30, 1993	Tang, et al.	—	—	
	8.	5,714,415	February 3, 1998	Oguro	—	—	
	9.	6,410,434	June 25, 2002	Mani	—	—	
	10.	6,723,621	April 20, 2004	Cordone, et al.	—	—	
	11.	6,897,471	May 24, 2005	Soref, et al.	—	—	
	12.	6,441,716	August 27, 2002	Doppalapudi, et al.	—	—	

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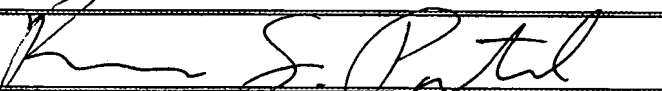
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FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
RSP	13.	WO 2005/001902	January 6, 2005	PCT	—	—		
	14.	WO 2004/114368	December 29, 2004	PCT	—	—		
	15.	WO 2005/015609	February 17, 2005	PCT	—	—		
	16.	WO 2003/033781	April 24, 2003	PCT	—	—		
↓	17.	WO 2006/009171	January 26, 2006	PCT	—	—		

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc).

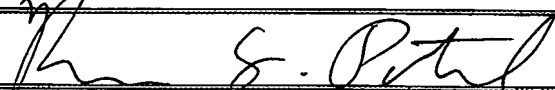
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RSP	18.	D. W. Jenkins, "Electronic properties of metastable GexSn1-x alloys", Phys. Rev. B., Vol: 36, pp. 7994-8001 (1987).
	19.	K. A. Mader, "Band structure and instability of GexSn1-x alloys", Solid State Commun., Vol: 69 (12), pp. 1123-1126 (1989).
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RSP	21.	O. Gurdal, R. Desjardins, J. R. A. Carlsson, N. Taylor, H. H. Radamson, J.-E. Sundgren, and J. E. Greene, "Low-temperature growth and critical epitaxial thicknesses of fully strained metastable Ge _{1-x} Sn _x (x ≤ 0.26) alloys", J. Appl. Phys., Vol: 83(1), pp. 162-170 (1998).
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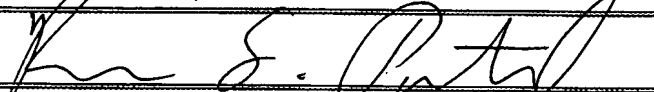
25P	31.	J. Taraci, S. Zollner, M. R. McCartney, J. Menéndez, M. A. Santana, D. J. Smith, A. Haaland, A. V. Tutukin, G. Gundersen, G. Wolf, and J. Kouvetakis, "Synthesis of silicon-based infrared semiconductors in the Ge-Sn system using molecular chemistry methods", J. of the Am. Chem. Soc., Vol: 123(44), pp. 10980-10987 (2001).
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RSP	39.	T G. Kresse and J. Hafner, "Ab initio molecular dynamics for liquid metals", Phys. Rev. B47(1), pp. R558-561 (1993).
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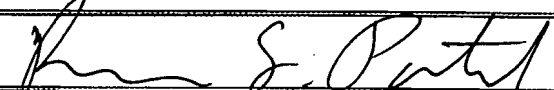
RSP	49. E. A. V. Ebsworth, D. J. Hutchison, D. W. H. Rankin, "The Preparation, properties, and Gas-Phase Molecular-Structure of 1,1- Difluoro-2,2-Digermylbiphosphone", J. Chem. Res., Synop, 12, pp. 393, (1980).
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RSP	59.	G. Davidson, L. A. Woodward, E. A. V. Ebsworth, G. M. Sheldrick, "The vibrational spectra and structure of trisilylarsine and trisilylstibine", Spectrochim. Acta, Part A, Vol: 23, pp. 2609-2616, (1967).
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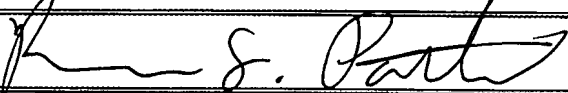
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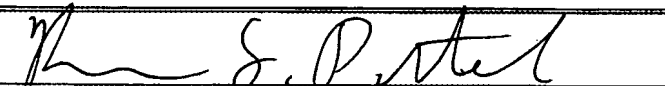
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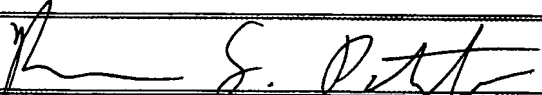
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FORM PTO-1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No.	Serial No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		05-720-US2	10/559,981
		Applicant:	
		Kouvetakis, et al.	
		Filing Date:	Group:
		December 8, 2005	2812

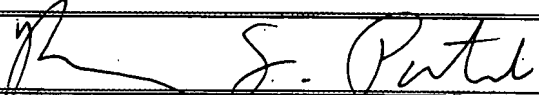
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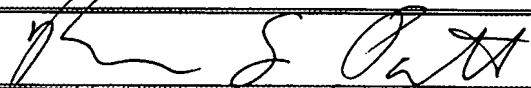
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		Kouvetakis, et al.		
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		December 8, 2005	2812	

COMMONLY OWNED CO-PENDING APPLICATIONS

Examiner Initial		
RJP	1.	Kouvetakis, et al., U.S. Patent Application No. 10/559,980, Filed on December 8, 2005.
RJP	2.	Kouvetakis, et al., U.S. Patent Application No. 10/559,979, Filed on December 8, 2005.

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